

Advanced Low-Cost SiC and GaN Wide Bandgap Inverters for Under- the-Hood Electric Vehicle Traction Drives

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Project ID: EDT058

This presentation does not contain any proprietary, confidential, or otherwise restricted information.

Timeline

Project Start Date: October 1, 2013
Project End Date: December 30, 2015
Percent Complete: 100%

Budget

Total Project Funding: \$3.8M

- **Non-Federal Share:** \$2.0M
- **Federal/DOE Share:** \$1.8M
 - Funding in FY14:** \$1,170,086
 - Funding in FY15:** \$ 630,046

Barriers

- Unit cost \leq \$182 / 100,000
- Obtaining high-volume cost information
- High-current GaN HEMT device availability and maturity

Partners

- Toyota - TRINA
- GaN Systems, Inc.
- National Renewable Energy Laboratory
- University of Arkansas National Center for Reliable Electric Power Transmission

RELEVANCE: OBJECTIVES

- Develop two independent 55 kW peak traction inverter designs (one SiC based and one GaN based) to showcase the performance capabilities of WBG power devices – namely high efficiency, increased gravimetric and volumetric density through high operating junction temperature capability.
- Demonstrate a substantial cost reduction from the die level to the system level.
- Optimize proven productized high-temperature WBG power modules for increased manufacturability and reduced cost.
- Application of advanced system-level packaging techniques to completely eliminate a vehicle's secondary cooling loop system; utilize 85 °C rated capacitors, reduce interconnects, and enable increased system reliability.
- Demonstrate design robustness and reliability through extended testing of subsystems and systems under realistic application operating conditions.

RELEVANCE: OBJECTIVES

- Application of advanced system-level packaging techniques to completely eliminate a vehicle's secondary cooling loop system, utilize 85°C rated capacitors, reduce interconnects, and enable increased system reliability.
- Demonstrate design robustness and reliability through extended testing of subsystems and systems under realistic application operating conditions.
- Complete cost and manufacturing analysis to aid commercialization effort.

The goal of this research is to **reduce traction inverter size** (≥ 13.4 kW/L), **weight** (≥ 14.1 kW/kg), and **cost** ($\leq \$182 / 100,000$) while maintaining 15 year reliability metrics.

RELEVANCE

The *USDRIVE* Electrical and Electronics Technical Team's mission is to enable **cost-effective (A)**, **smaller, lighter (C)**, and **efficient (E)** power electronics and electric motors for electric traction drive systems.

The DOE EE&RE Vehicle Technologies Program Multi-Year Program Plan (2011-2015) states power electronics technology targets of **\$3.30/kW (A)**, **14.1 kW/kg (C)**, and **13.4 kW/l** by 2020 to reduce dependence on oil through electrification of vehicle drives with **15-year life (D)**.

Requirement	Target
Continuous power output (kW)	30
Peak power output for 18 seconds (kW)	55
Weight (kg)	≤ 3.9
Volume (l)	≤ 4.1
Efficiency	> 93%
Unit cost for quantities of 100,000 (\$)	≤ 182
Operating voltage (Vdc)	200 to 450; nominal: 325
Power factor of load	> 0.8
Maximum current per phase (Arms)	400
Pre-charge time – 0 to 200 Vdc (sec)	2
Output current ripple – peak to peak (% of fundamental peak)	≤ 3
Maximum switching frequency (kHz)	20
Current loop bandwidth (kHz)	2
Maximum fundamental electrical frequency (Hz)	1000
Minimum isolation impedance-input and phase terminals to ground (MΩ)	1
Minimum motor input inductance (mH)	0.5
Ambient operating temperature (°C)	-40 to +140

TECHNICAL APPROACH / STRATEGY

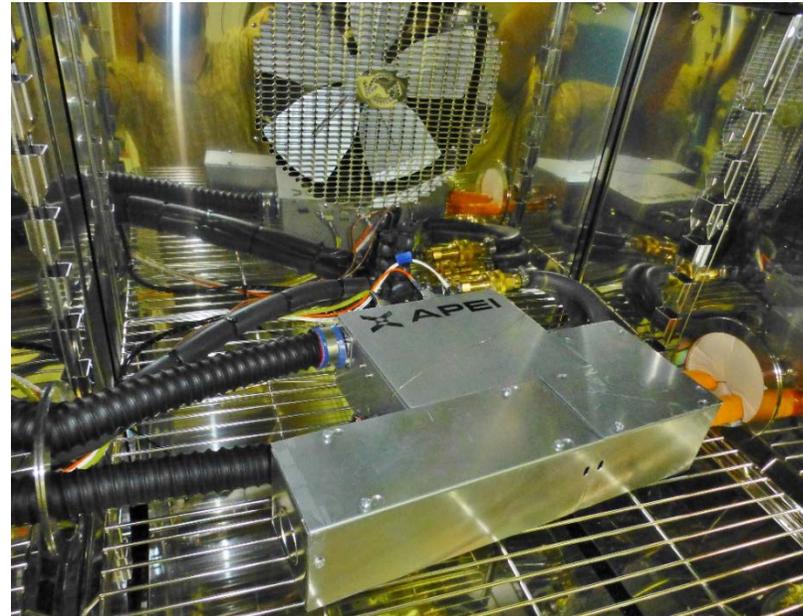
- This program will develop two completely independent WBG traction inverters: one **SiC based** and one **GaN based**. This work will provide a unique, **direct comparison** between **inverter designs using SiC and GaN**. (Wolfspeed)
- This program will advance GaN HEMT power semiconductor device technology to **600 V, 100 A**. (GaN Systems)
- This program will utilize advanced **high performance power modules** to achieve high power density and efficiency. (Wolfspeed)
- This program will use **advanced packaging techniques** (Wolfspeed) and **active cooling technologies** (Toyota, NREL) to enable the use of low-cost, 85 °C-rated DC bus capacitors.
- **Custom, in-house HTSOI IC designs** will dramatically reduce the cost of high temperature capable support circuitry. (Wolfspeed, *abandoned*)

Technical Accomplishments: Results vs. AOI 12 Targets

HIGH-POWER DYNAMOMETER TEST BED AT THE UNIVERSITY OF ARKANSAS NATIONAL CENTER FOR RELIABLE ELECTRIC POWER TRANSMISSION



A view of the test bed beside the ABB/Baldor drive applying torque commands to the induction machine to load the interior PMSM



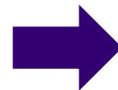
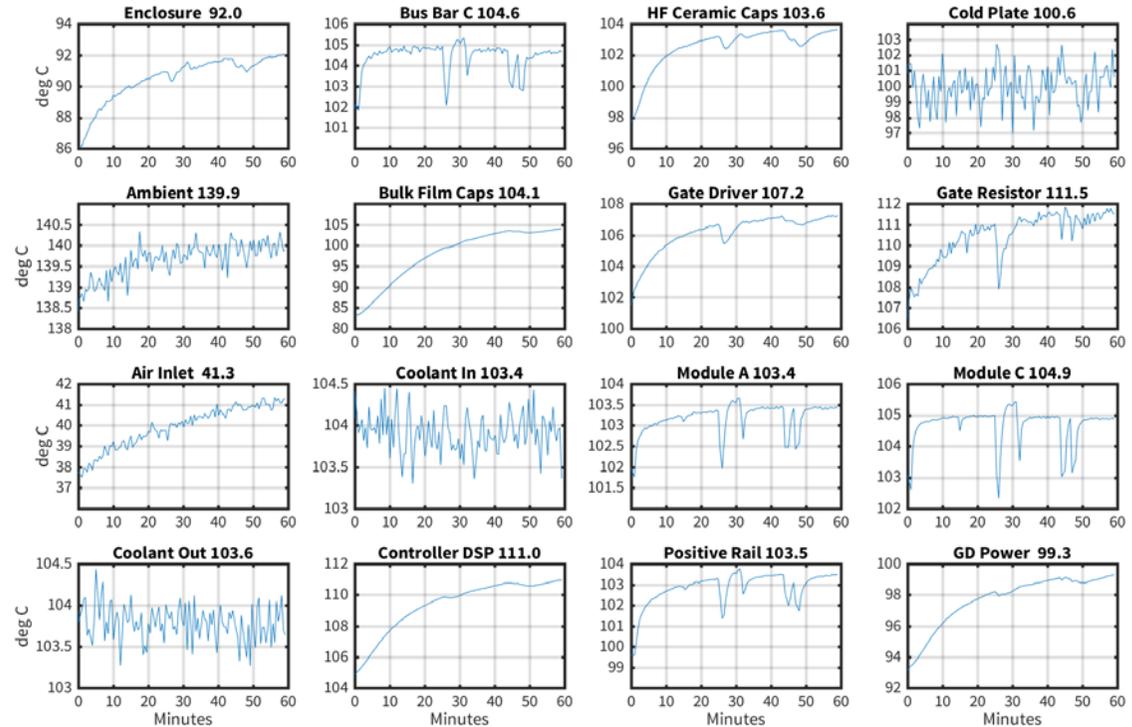
The Design Cycle 2 SiC inverter inside the environmental chamber ready for test

ACCOMPLISHMENTS VERSUS PROGRAM TARGETS

No.	Requirement	Target	SiC-Based Inverter	GaN-Based Inverter
1	Continuous power output (kW)	30	√+	√
2	Peak power output for 18 seconds (kW)	55	√+	√
3	Weight (kg)	≤ 3.9	√	√
4	Volume (l)	≤ 4.1	√	√
5	Efficiency	> 93%	√+	Unknown
6	Unit Cost for quantities of 100,000 (\$)	≤ 182	√+	√
7	Operating voltage (V dc)	200 to 450; nominal: 325	√+	√
8	Power factor of load	> 0.8	√	√
9	Maximum current per phase (Arms)	400	√	√
10	Pre-charge time – 0 to 200 V dc (sec)	2	√	√
11	Output current ripple – peak to peak (% of fundamental peak)	≤ 3	√	√
12	Maximum switching frequency (kHz)	20	√+	√+
13	Current loop bandwidth (kHz)	2	√+	√+
14	Maximum fundamental electrical frequency (Hz)	1000	√+	√+
15	Minimum isolation impedance-input and phase terminals to ground (MΩ)	1	√	√
16	Minimum motor input inductance (mH)	0.5	√	√
17	Ambient operating temperature (°C)	-40 to +140	√	√

CONTINUOUS POWER OUTPUT TARGET = 30 kW

- Thermal steady-state
- 59 minutes in duration
- 30 kW, 27 kVAr, 40 kVA @ 3480 RPM and 72 N-m load
- DPF ~ 0.75 lagging
- 105 °C coolant
- 140 °C ambient
- 40 °C air
- 450 VDC bus
- 16 thermocouples throughout the inverter system and averaged temperatures were recorded every 30 seconds

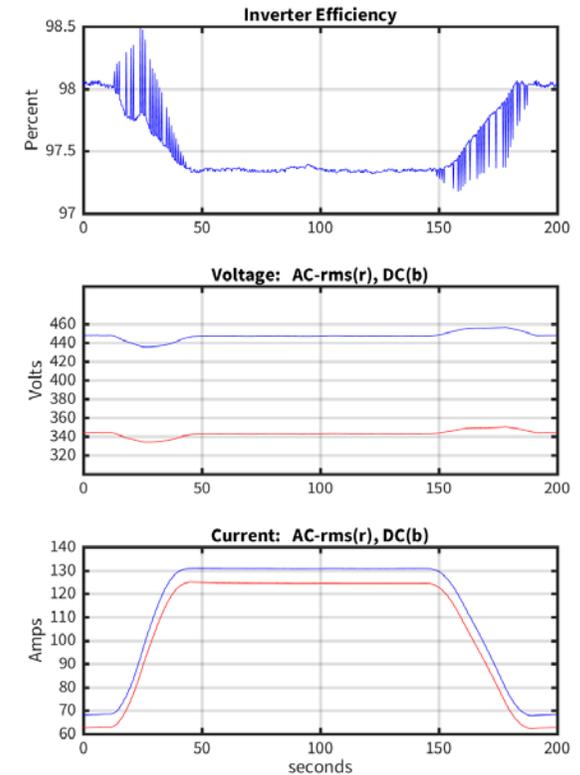
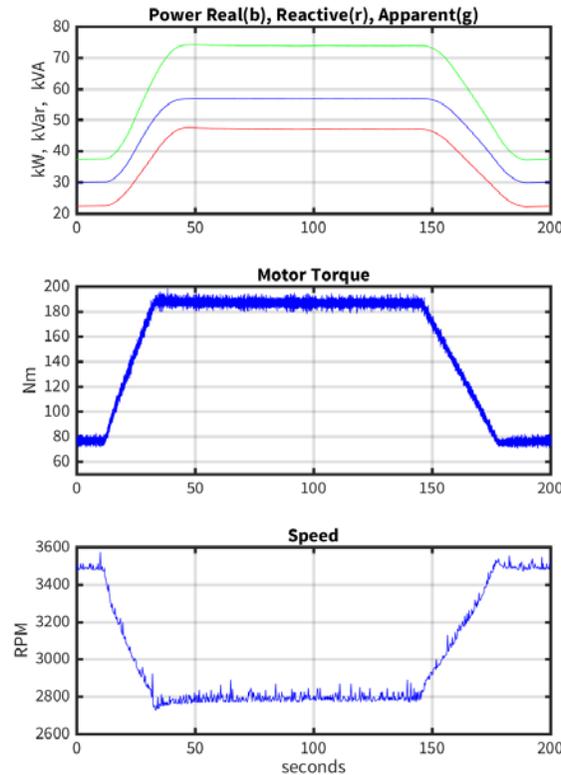


K	-200°C to 1250°C (-328° F to 2282°F)	Greater of 2.2°C or 0.75%	Greater of 1.1°C or 0.4%
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Source: www.omega.com

PEAK POWER OUTPUT FOR 18 SECONDS TARGET = 55 kW

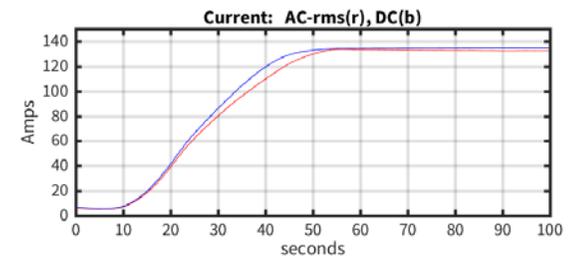
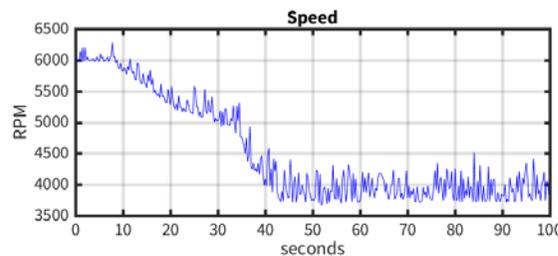
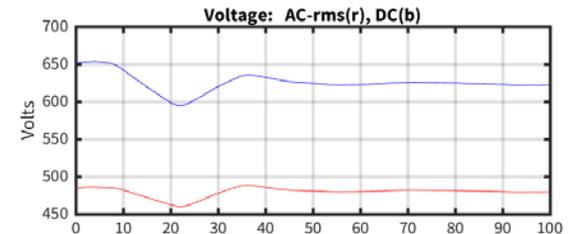
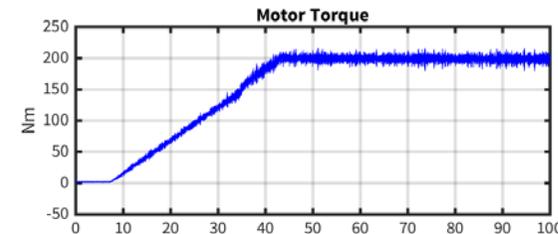
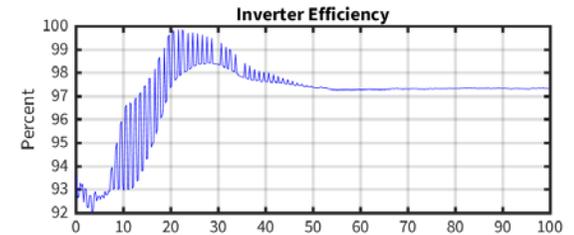
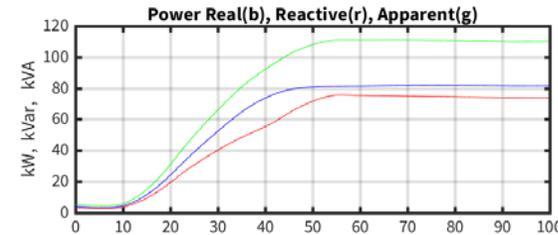
- Thermal steady-state @ 30 kW
- Load is raised to 55 kW for a finite duration, and then lowered back to 30 kW
- 105 °C coolant
- 140 °C ambient
- 40 °C air
- 450 VDC bus
- 56.9 kW, 47.3 kVAr, 74 kVA, 97.3%
- Test was repeated three times dwelling for 50, 60, and then 120 seconds



MAXIMUM POWER (NO TARGET) = 81.8 kW

- Find the maximum continuous power for computing power density and specific weight
- Physical limitations existed: DC bus voltage, torque transducer, flexible shaft couplers
- **1st attempt: 650 VDC, 6000 RPM, and 180 N-m of load torque**
- **81.8 kW, 74.7 kVAr, and 110 kVA**
- DPF = 0.738 lagging
- $\eta = 97.4\%$
- **~60 seconds**
- $dV/dt = 650/50n = 13 \text{ kV}/\mu\text{s}$!
- EMI caused communication failures and locked up the GUI

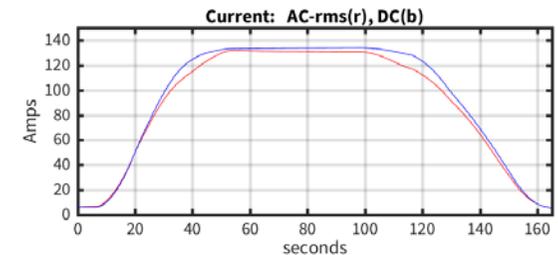
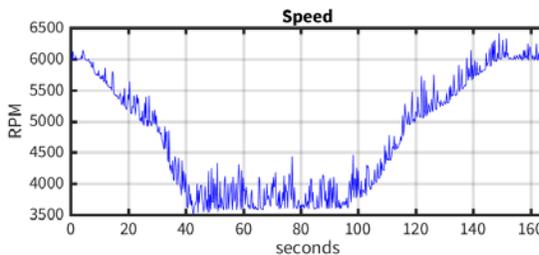
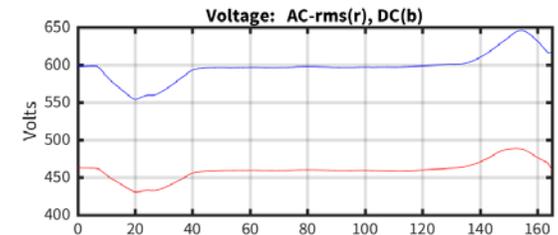
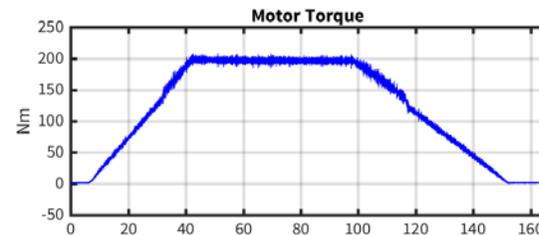
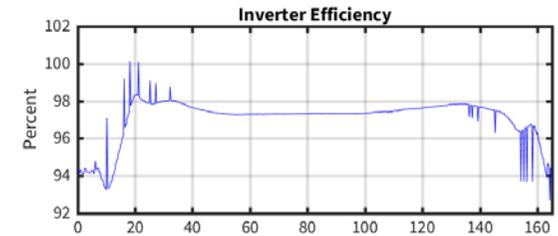
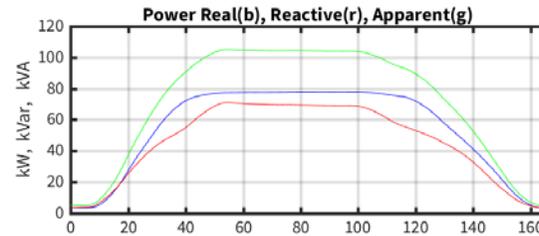
DYNAMOMETER LIMITED!



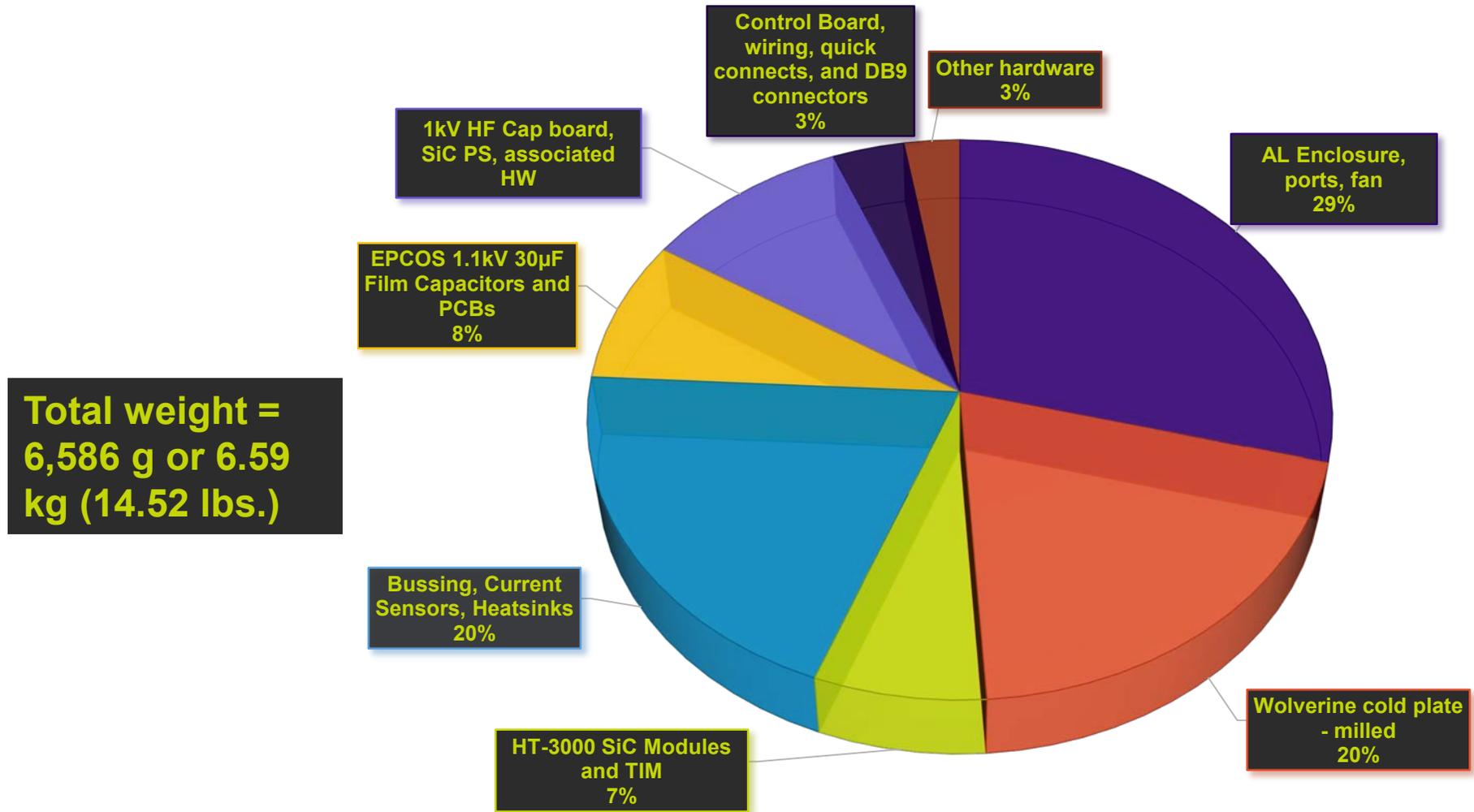
MAXIMUM POWER TARGET = 77.9 kW

DYNAMOMETER LIMITED!

- 2nd attempt: 600 VDC, 6000 RPM, and 180 N-m of load torque
- 77.9 kW, 69.1 kVARs, and 104 kVA
- DPF = 0.748 lagging
- $\eta \geq 97.4\%$
- Ran 3 times: 1, 2, and 3 minutes
- $dV/dt = 600/50n = \text{still } 12 \text{ kV}/\mu\text{s}!$
- DC bus caps reached their rating

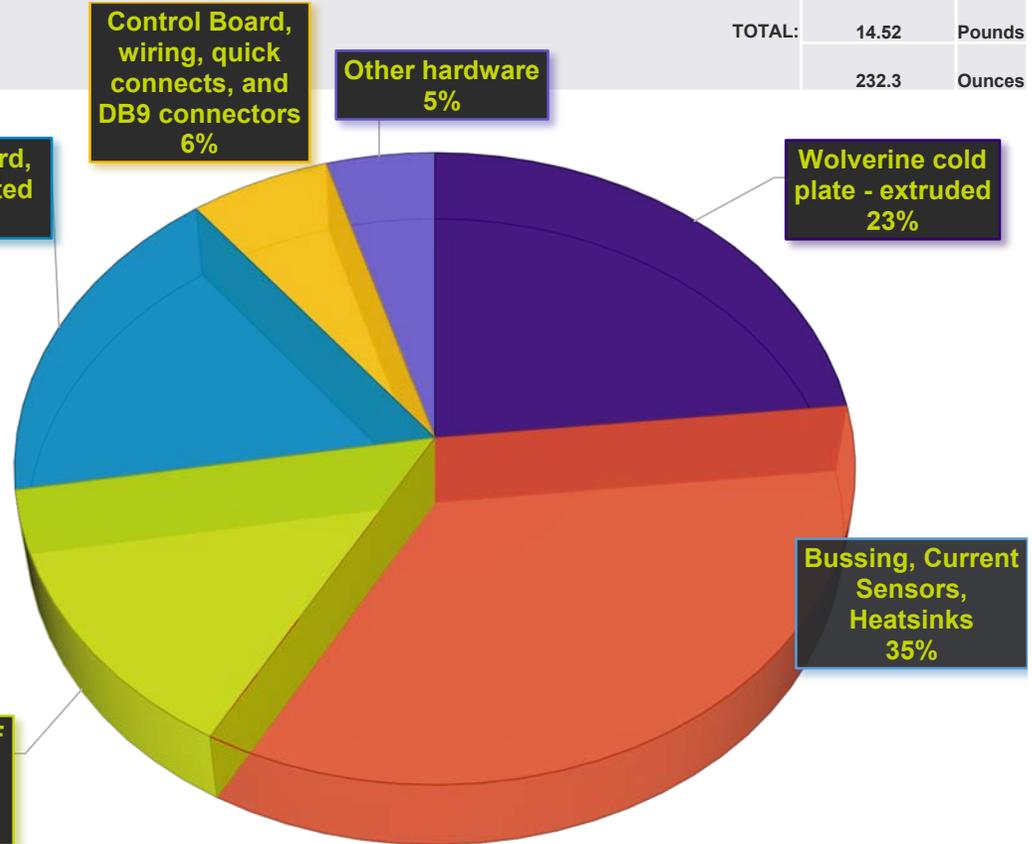


SiC INVERTER WEIGHT TARGET $\leq 3,900 \text{ G} = 3.9 \text{ KG}$



SiC INVERTER WEIGHT TARGET ≤ 3,900 G = 3.9 KG, CONT.

DOE VTP - Phase 1 Inverter Weights				
Item Description	Grams	Qty	Component Total	Unit
AL Enclosure, ports, fan	1909	1	1909	Grams
Wolverine cold plate - milled	1315	1	1315	Grams
HT-3000 SiC Modules and TIM	150	3	450	Grams
Bussing, Current Sensors, Heatsinks	1323	1	1323	Grams
EPCOS 1.1kV 30µF Film Capacitors and PCBs	90	6	540	Grams
1kV HF Cap board, SiC PS, associated HW	216	3	648	Grams
Control Board, wiring, quick connects, and DB9 connectors	226	1	226	Grams
Other hardware	175	1	175	Grams
			6,586	Grams
			TOTAL:	14.52 Pounds
				232.3 Ounces



NOTE:

- Remove enclosure base, silicone sealer, lid, ports, hardware, and fan (-1909 g)
- Remove milled Wolverine cold plate (-1315 g)
- Add Wolverine extruded cold plate (+887 g)
- Remove three of six DC bus caps (-270 g)

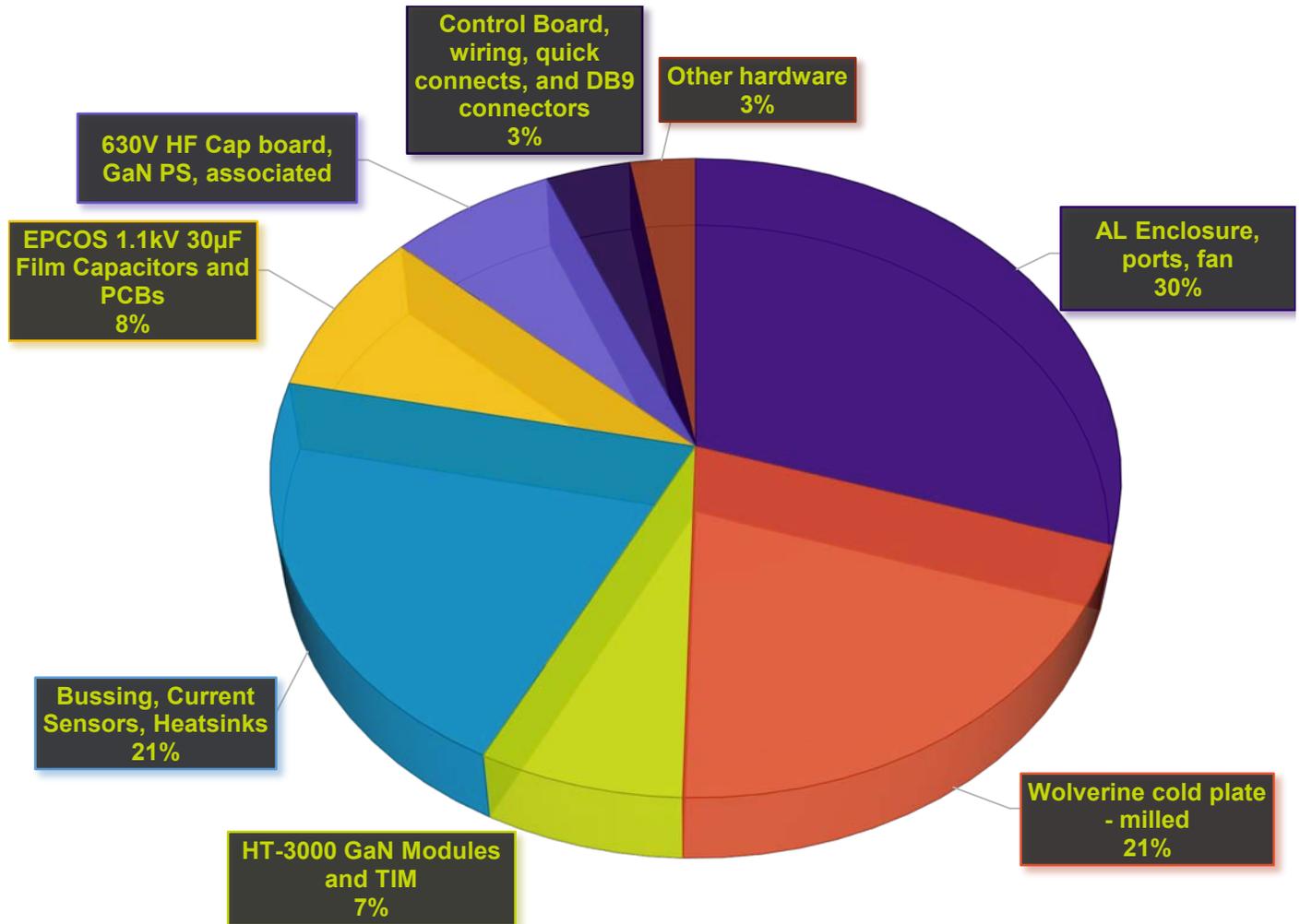
New TOTAL = 3,979 g = 3.98 kg (8.77 lbs.)

TARGET ≤ 3,900 g = 3.90 kg

GaN INVERTER WEIGHT TARGET $\leq 3,900 \text{ G} = 3.9 \text{ KG}$

**Total weight =
6,392 g or 6.39
kg (14.09 lbs.)**

**The SiC inverter
weighs slightly
more than the
GaN inverter
because the 1 kV
HF MLCC X7R
capacitors are
physically larger
than the ones
rated at 630 V.**



GaN INVERTER WEIGHT TARGET

≤ 3,900 G = 3.9 KG CONT.

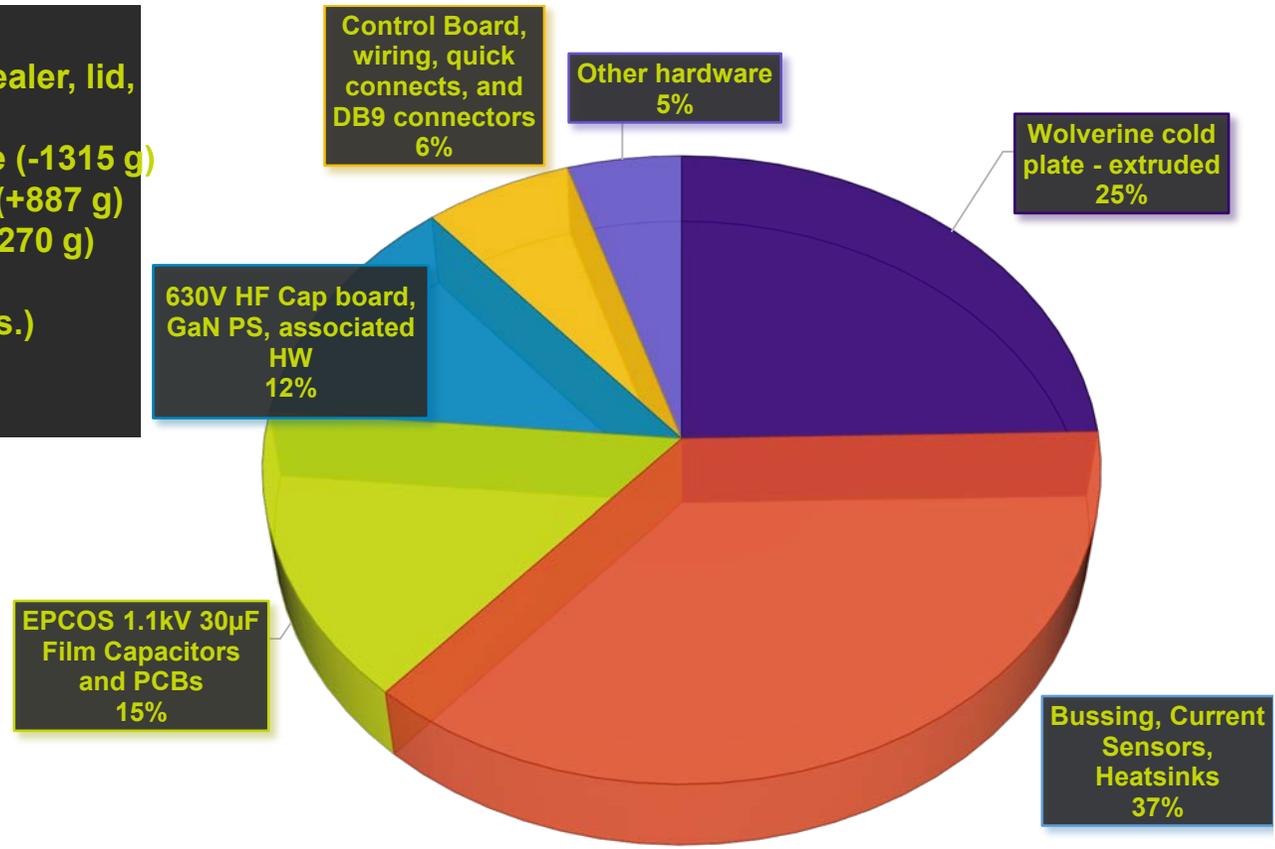
DOE VTP - Phase 1 Inverter Weights				
Item Description	Grams	Qty	Component Total	Unit
AL Enclosure, ports, fan	1909	1	1909	Grams
Wolverine cold plate - milled	1315	1	1315	Grams
HT-3000 GaN Modules and TIM	152	3	456	Grams
Bussing, Current Sensors, Heatsinks	1323	1	1323	Grams
EPCOS 1.1kV 30µF Film Capacitors and PCBs	90	6	540	Grams
630 V HF Cap board, GaN PS, associated HW	149	3	448	Grams
Control Board, wiring, quick connects, and DB9 connectors	226	1	226	Grams
Other hardware	175	1	175	Grams
			6,392	Grams
			TOTAL:	14.09 Pounds
				225.5 Ounces

NOTE:

- Remove enclosure base, silicone sealer, lid, ports, hardware, and fan (-1909 g)
- Remove milled Wolverine cold plate (-1315 g)
- Add Wolverine extruded cold plate (+887 g)
- Remove three of six DC bus caps (-270 g)

New TOTAL = 3,785 g = 3.79 kg (8.35 lbs.)

TARGET ≤ 3,900 g = 3.90 kg



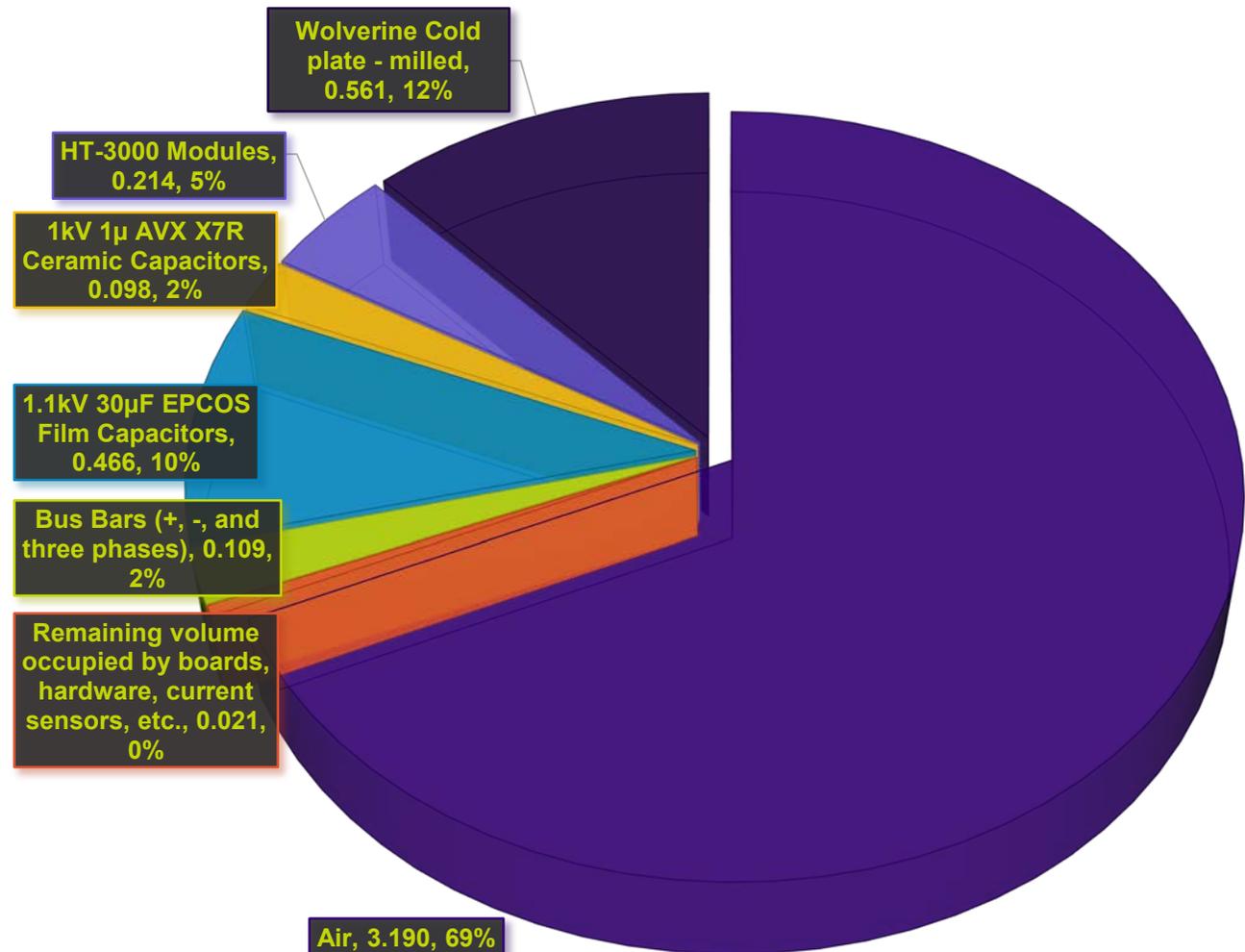
SiC & GaN INVERTER VOLUME TARGET ≤ 4.1 LITERS

Note: This air volume excludes the displacement caused by internal wiring and associated quick connectors.

Total external volume = 4.83 liters (excluding glands and connectors)

Total internal volume = 4.66 liters

With 1/2 the DC bus capacitors, 4.43 liters



POWER DENSITY TARGETS ≥ 13.4 KW/L & 14.1 KW/KG

Design Cycle 2 SiC Inverter, 4.8 L, 6.6 kg, HT-3201-R modules
@ max. ambient and coolant temperatures

kW	kVAr	kVA	kW/L	kW/kg	kVA/L	kVA/kg
30	27	40.4	6.2	4.5	8.4	6.1
56.9	47.3	74.0	11.8	8.6	15.4	11.2
77.9	69.1	104.2	16.2	11.8	21.7	15.8
81.8	74.7	110.8	17.0 	12.4 	23.1	16.8

2020 2015

Design Cycle 2 SiC Inverter, 4.4 L, 4.0 kg, HT-3201-R modules
@ max. ambient and coolant temperatures

kW	kVAr	kVA	kW/L	kW/kg	kVA/L	kVA/kg
30	27	40.4	6.8	7.5	9.2	10.1
56.9	47.3	74.0	12.9	14.2	16.8	18.5
77.9	69.1	104.2	17.7	19.5	23.7	26.0
81.8	74.7	110.8	18.6 	20.4 	25.2	27.7

2025 2025

THEORETICAL/ACHIEVABLE POWER DENSITY TARGETS ≥ 13.4 KW/L & 14.1 KW/KG

Design Cycle 2 SiC Inverter, 4.8 L, 6.6 kg , HT-3201-R modules @ < max. ambient & coolant temperatures

kW	kVAr	kVA	kW/L	kW/kg	kVA/L	kVA/kg
166.3	124.7	207.9	34.6	25.2	43.3	31.5
199.5	149.6	249.4	41.6 ★	30.2 ★	51.9	37.8

2025

2025

- With a DC bus of 650 VDC, the achievable AC output voltage is 400 V rms line to line.
- With a DC bus of 800 VDC, the achievable AC output voltage is 480 V rms line to line.
- Assume an achievable AC output current of 300 A rms and a worst-case DPF = 0.8.
- $P_{3\phi} = \sqrt{3} (400 [480]) (300) (0.8) = 166.3 \text{ kW} [199.5 \text{ kW}]$
- $Q_{3\phi} = \sqrt{3} (400 [480]) (300) (0.6) = 124.7 \text{ kVAr} [149.6 \text{ kVAr}]$
- The apparent power, $|S_{3\phi}| = 207.9 [249.4 \text{ kVA}]$

Design Cycle 2 SiC Inverter, 4.4 L, 4.0 kg , HT-3201-R modules @ < max. ambient & coolant temperatures

kW	kVAr	kVA	kW/L	kW/kg	kVA/L	kVA/kg
166.3	124.7	207.9	37.8	41.6	47.2	52.0
199.5	149.6	249.4	45.3 ★	49.9 ★	56.7	62.3

2025

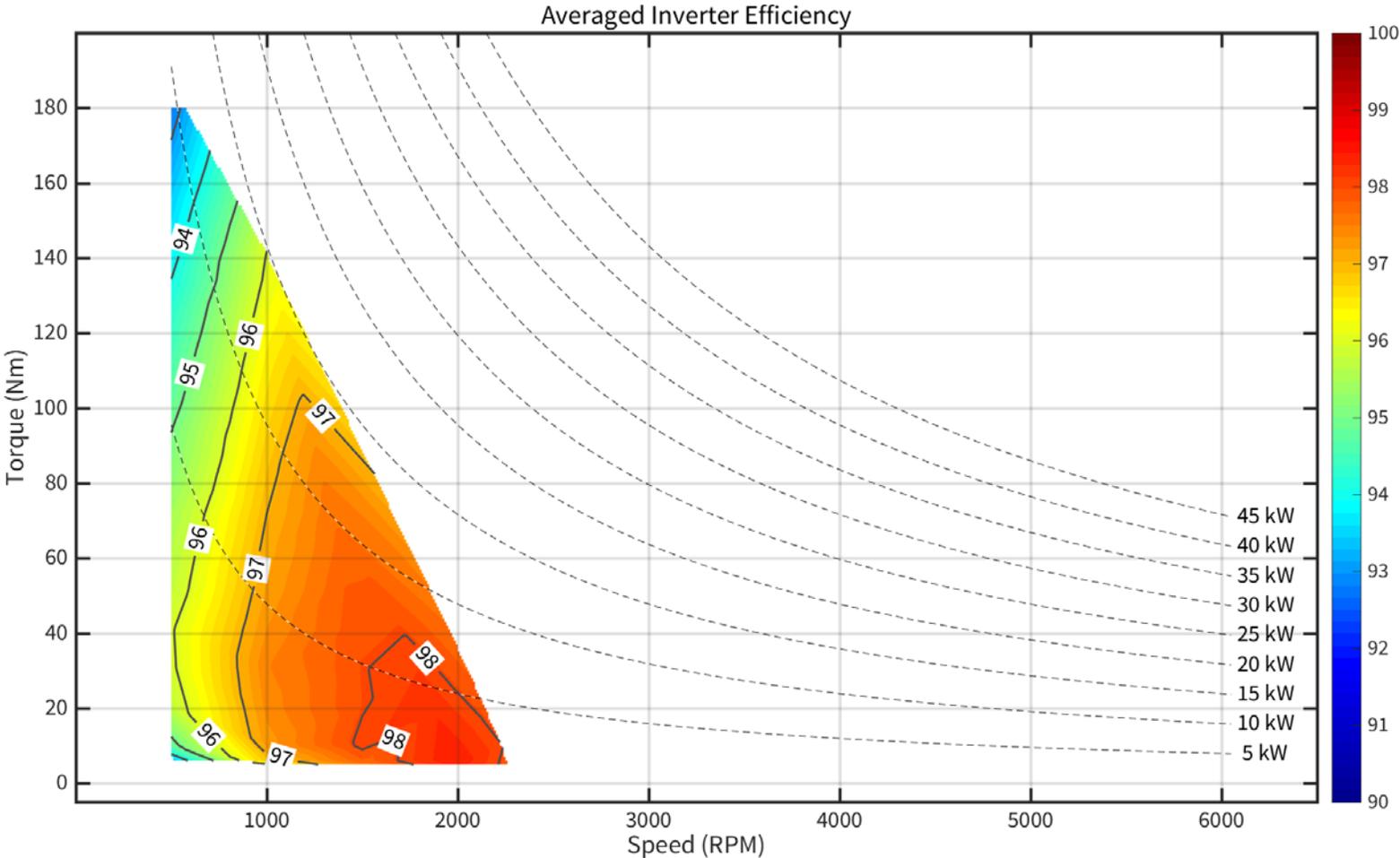
2025

SiC INVERTER EFFICIENCY TARGET > 93%, CONT.

- 650 V DC bus has a slightly lower efficiency
- “Sweet spot” may be outside the range of torques and speeds that were tested
- The nominal 325 V DC bus yielded the best overall efficiency
- Efficiencies measured at loads < 5 kW are not as reliable due to current signal scaling and its impact on the Yokogawa’s resolution being no greater than 10 W
- 200 VDC, 66 operating points
- 325 VDC, 135 operating points
- 450 VDC, 151 operating points
- 650 VDC, 155 operating points
- 4 bus voltages, 507 operating points
- 6 thermal cases: 3,042 operating points

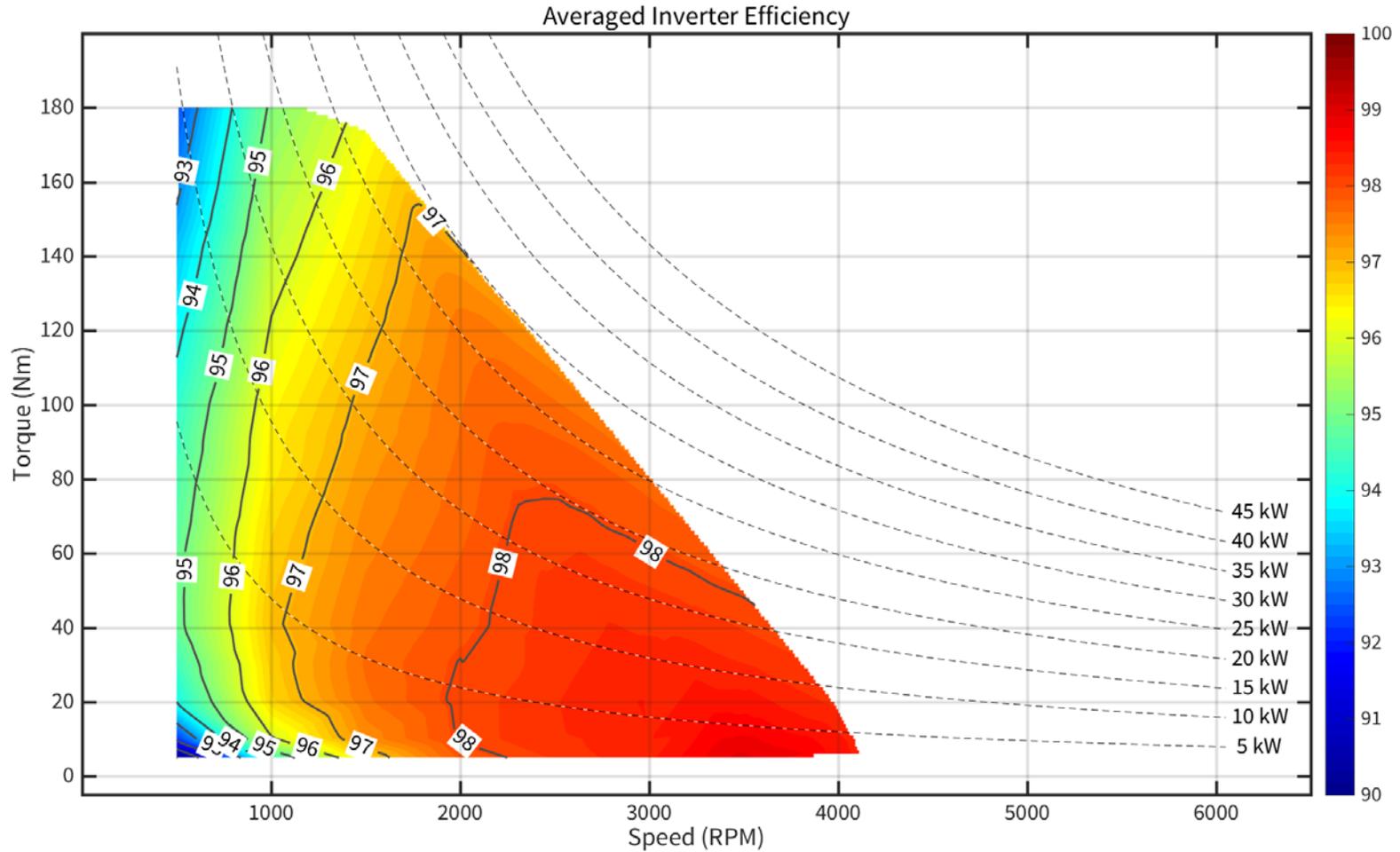
Bus Voltage	Average Efficiency (%)	Peak Efficiency (%)
200	96.7	98.7
325	97.0	99.0
450	96.3	98.2
650	95.2	97.9
All 4	96.3	98.9

SIC INVERTER EFFICIENCY TARGET > 93%



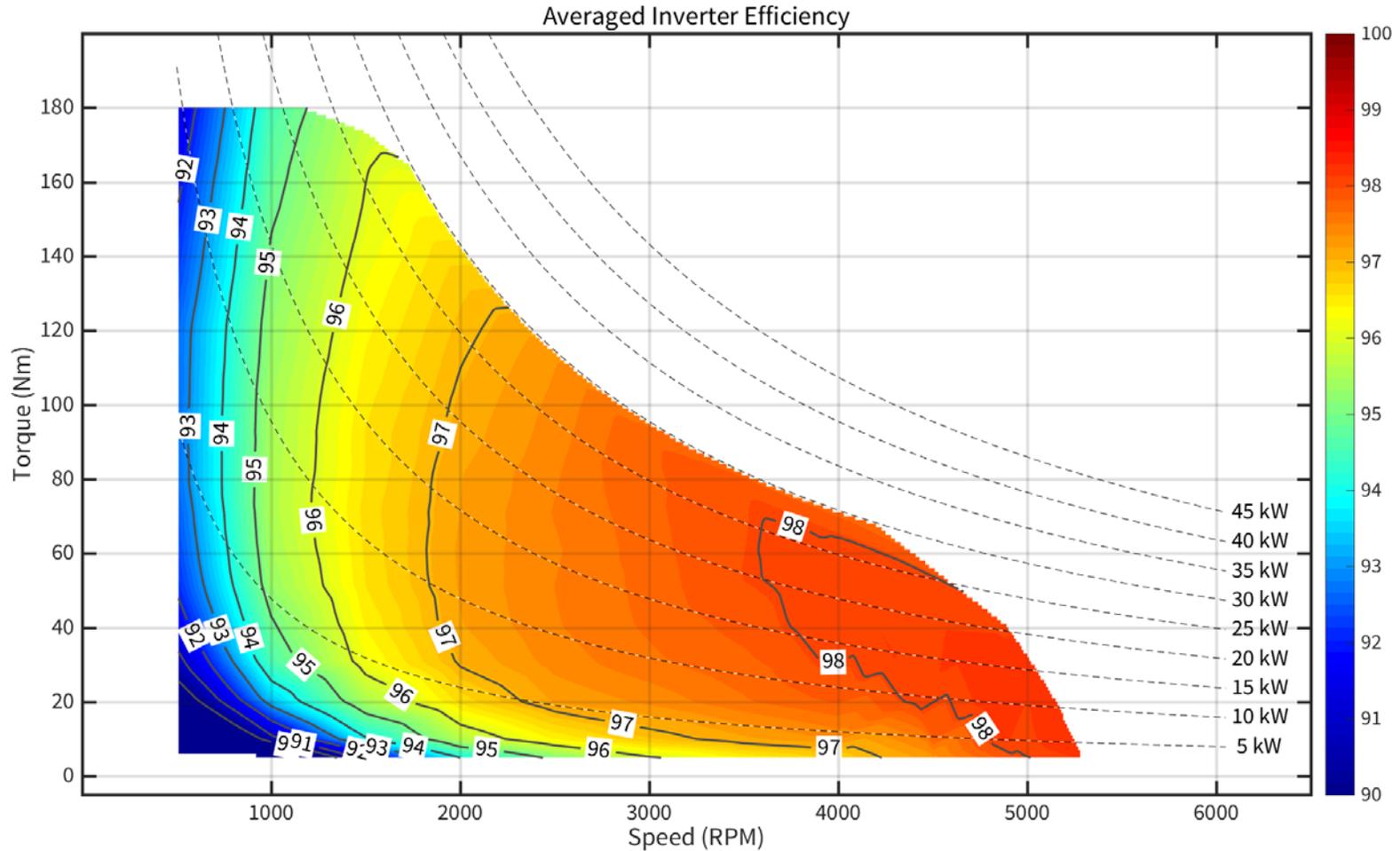
Average of 6 thermal cases, 200 VDC, Mean = 96.7%, Peak = 98.4%

SIC INVERTER EFFICIENCY TARGET > 93%, CONT.



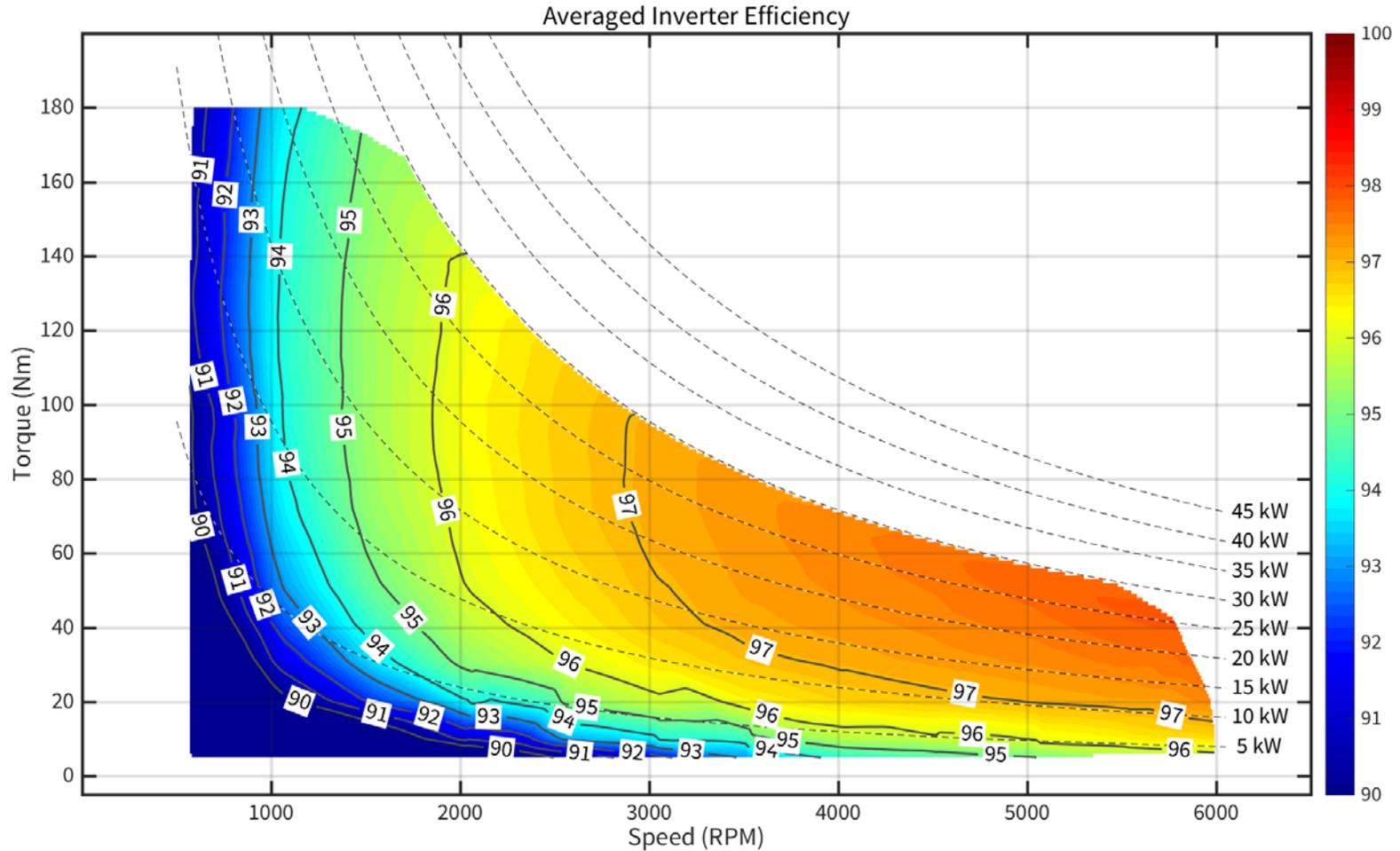
Average of 6 thermal cases, 325 VDC, Mean = 97.0%, Peak = 99.0%

SIC INVERTER EFFICIENCY TARGET > 93%, CONT.



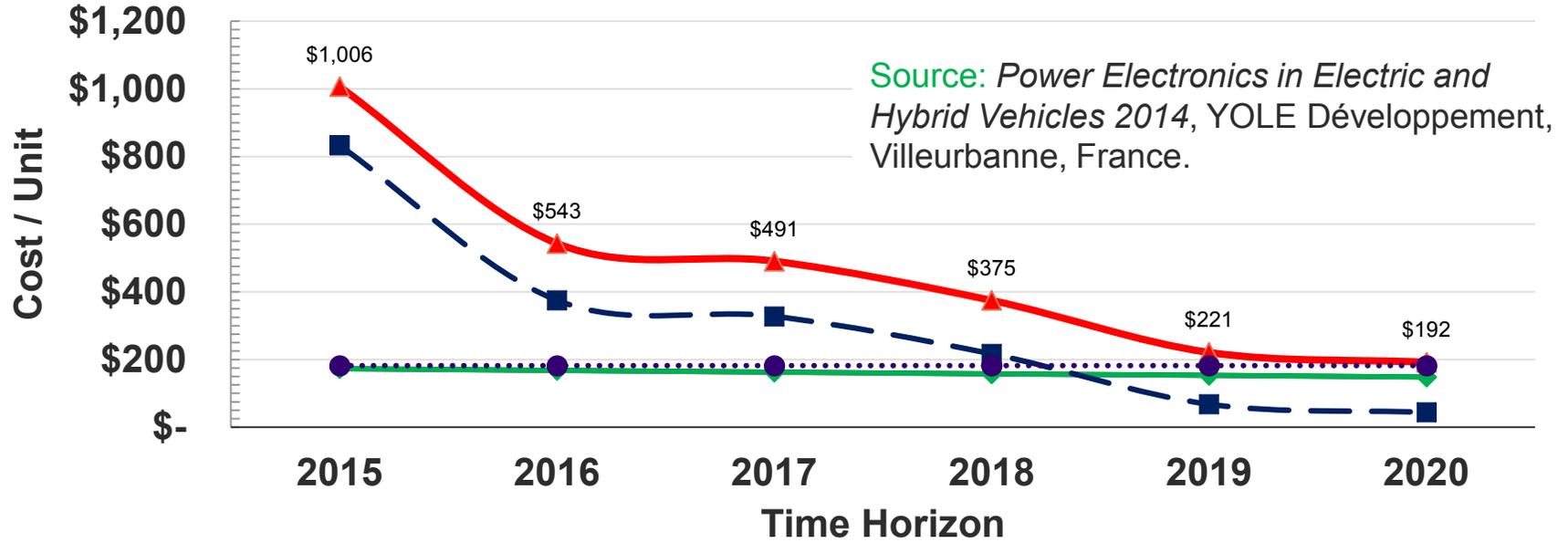
Average of 6 thermal cases, 450 VDC, Mean = 96.2%, Peak = 98.2%

SIC INVERTER EFFICIENCY TARGET > 93%, CONT.



Average of 6 thermal cases, 650 VDC, Mean = 94.9%, Peak = 97.9%

SiC INVERTER COST BREAKDOWN



▲ Total Price of 60 kW SiC MOSFET HEV Inverter - Agarwal Price Projections

◆ Price of 60 kW SiC MOSFET HEV Inverter Cost Less SiC MOSFETs and SBDs

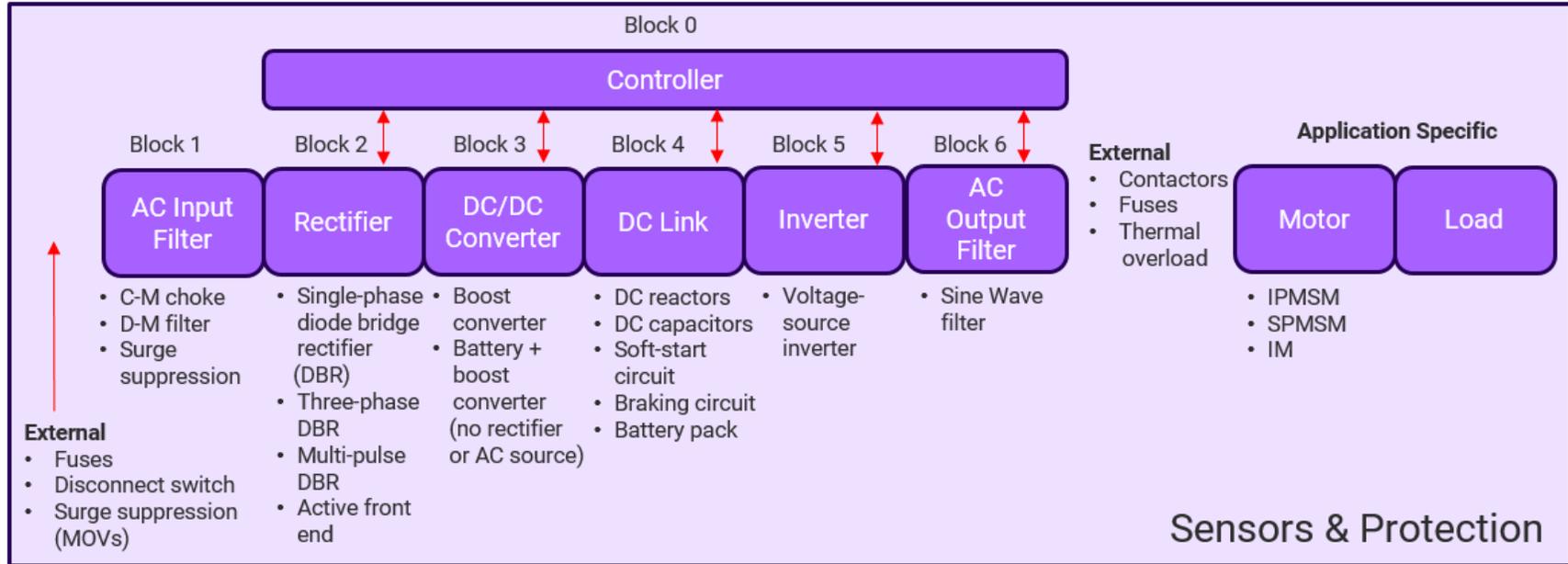
■ Agarwal's Projection for SiC Costs

● DOE Inverter Target, \$182

Source: A. K. Agarwal (DOE), "Manufacturing Perspective on Wide Bandgap Devices," MRS 2014, Session T6: SiC Power Devices, December 3, 2014.

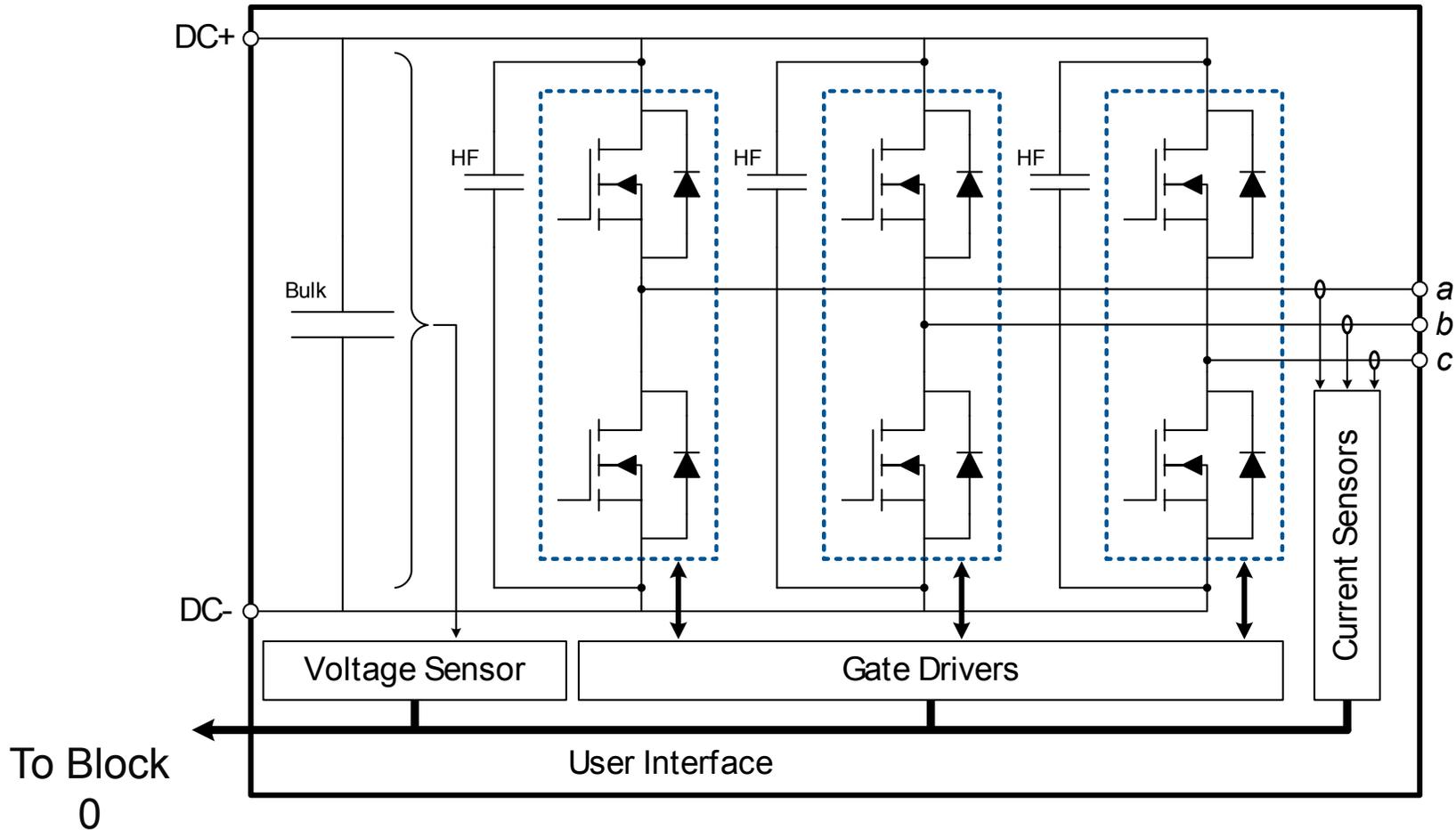
Commercialization Activity

PATH TO PRODUCT MANUFACTURING AND COMMERCIALIZATION



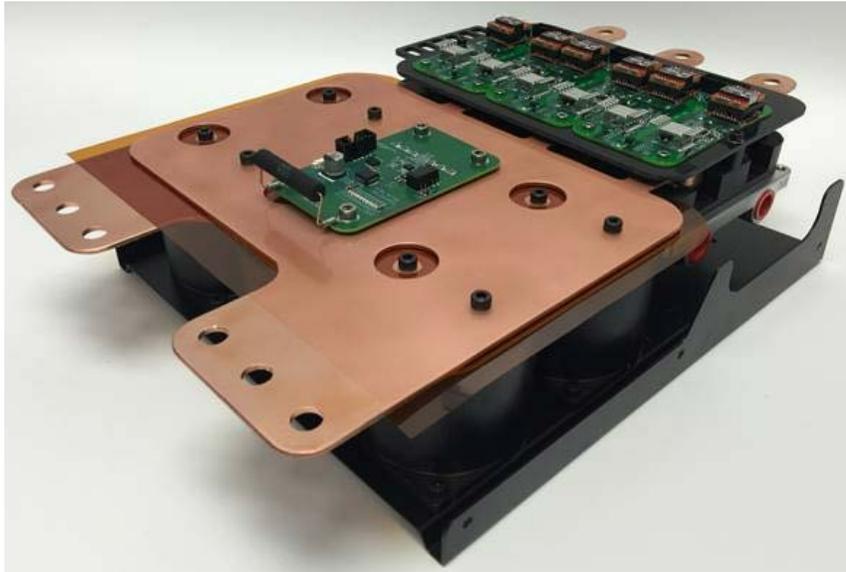
- Wolfspeed-led education initiative for WBG semiconductor adoption
- Building block philosophy (e.g., ONR’s PEBB initiative from many years ago)
- A highly WBG-optimized stack up that allows the user to “plug and play” in order to show ROI / PP on either legacy product designs or new product development
- We leveraged what we learned herein to focus on Blocks 0, 4, and 5
- Block 2 and Block 5 differ only by sensor suite
- Example: Block 0 + Block 2 + Block 4 + Block 5 give use an industrial motor drive

PATH TO PRODUCT MANUFACTURING AND COMMERCIALIZATION, CONT.



A Circuit Schematic of Blocks 4 and 5

PATH TO PRODUCT MANUFACTURING AND COMMERCIALIZATION, CONT.



Prototype build of Blocks 4 and 5 – Block 0 is not shown.

Questions and/or comments can be classified into one of two areas: (i.) **Production costing**; and (ii.) **EMI issues**.

Wolfspeed's Response: (i.) Three data points have been provided in this AMR presentation: the BOM costs for the Design Cycle 1 SiC inverter; the BOM costs for the Design Cycle 2 SiC inverter; and the Design Cycle 2 SiC inverter builds for N = 20, 50, 100, and 300. Further refinement will best be done after another design cycle is complete in concert with either an OEM or a Tier 1 supplier with a known insertion platform identified. Significant cost savings may be achieved if the maximum ambient temperature is relaxed from 140 °C to 125 °C.

Wolfspeed's Response: (ii.) The reviewer's are correct in pointing out EMI challenges associated with WBG semiconductors. But, any power device technology exhibiting "ideal power switch" characteristics and attributes will have similar challenges. As such, the system designer must be diligent in all aspects of grounding and shielding between, among, and within assemblies and subassemblies. Wolfspeed had to overcome numerous obstacles to achieve the electro-thermal targets of the program. For example, no 140 °C shielded inverter-grade cables were found. This necessitated designing and building our own.

COLLABORATIONS AND COORDINATION WITH OTHER INSTITUTIONS

- OEM – Toyota. Toyota collaborated on system-level **specifications** and on the design of the **thermal management system**.
- Device Manufacturer – GaN Systems, Inc. GaN Systems were to fabricate and test ≥ 600 V, ≥ 50 A **GaN HEMTs**.
- Supporting Research Organizations
 1. National Renewable Energy Laboratory – NREL performed **thermal and reliability analysis** at the module- and system-levels, respectively.
 2. University of Arkansas NCREPT – UA NCREPT assisted in the extensive **characterization and testing** of the traction inverter system using a custom-designed dynamometer test bed.

PROPOSED FUTURE WORK

- This project is complete as of December 31, 2015. Reporting continues.
- Candidate future work will be continued either through other DOE funding, or future IR&D funding
 - Package Si IGBTs within the HT-3000 package to overlay T vs. ω -plane efficiencies with those presented herein
 - Optimize the DC bussing for maximum current throughput with minimum temperature rise
 - Optimize the AC bussing for maximum current output with minimum temperature rise
 - Design using 1700 V creepage and clearance rules
 - Migrate design from Gen2 to Gen3 SiC MOSFETs
 - Design, build, and test efficacy of EMI enclosure for local controller
 - Design, build, and test efficacy of EMI enclosure for the power stage
 - Design, build, and test efficacy of output filter between inverter and traction motor
 - Others...

PROJECT SUMMARY

Source photo courtesy of Toyota.

Wolfspeed WBG Traction Inverters

- Two independent designs: SiC and GaN
- >98% Peak Efficiency
 - Fuel savings and reduced emissions
- \$182 cost at volume
- 15 Year Reliability



Wolfspeed
A CREE COMPANY

TOYOTA

GaN Systems

NREL
NATIONAL RENEWABLE ENERGY LABORATORY

UNIVERSITY OF ARKANSAS

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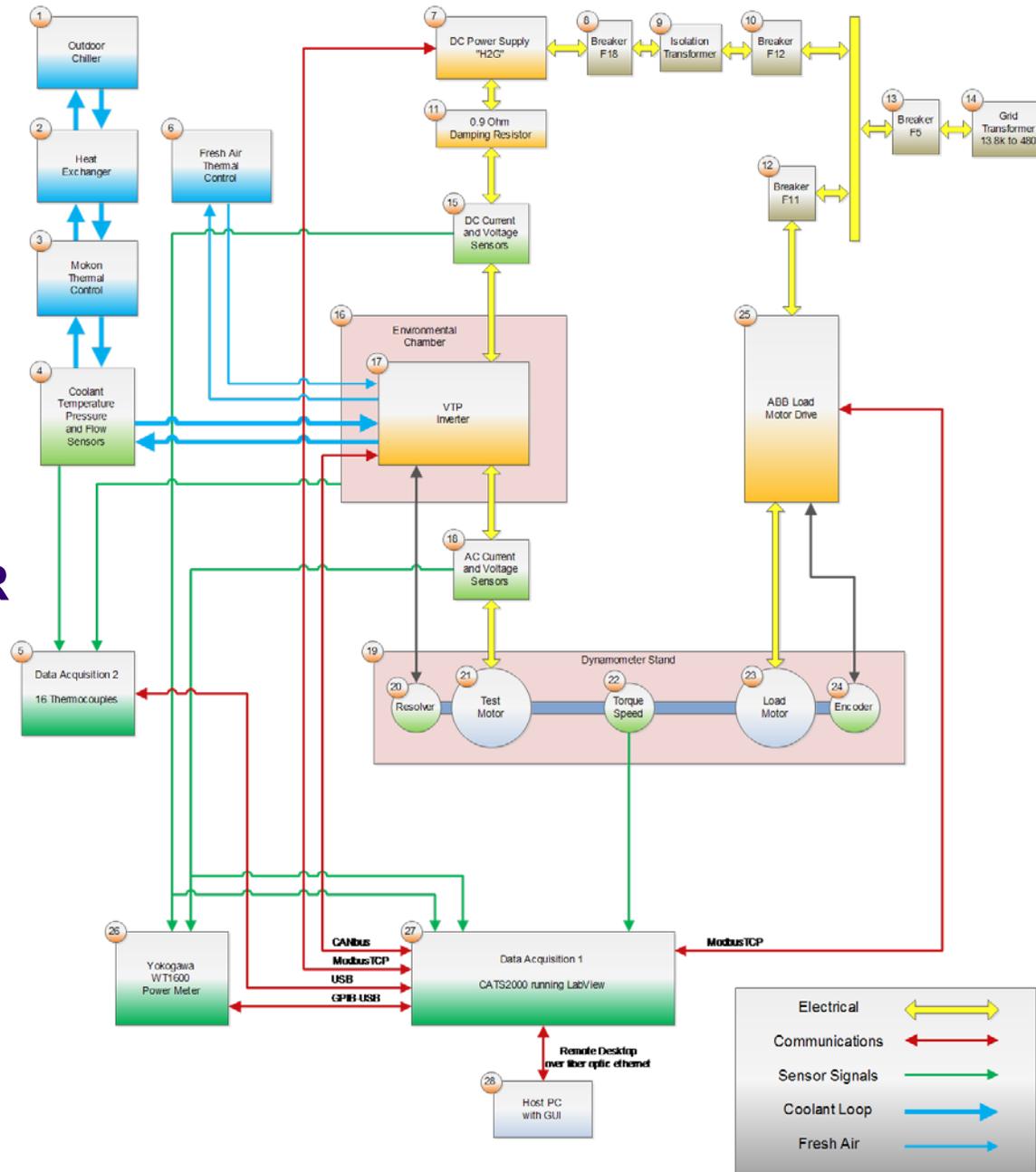
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 - Chris Farnell, Test Engineer
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Questions?

Technical Back-Up Slides

UA NCREPT HIGH POWER DYNAMOMETER



OPERATING VOLTAGE, TARGET = 200 TO 450 VDC; NOMINAL: 325 VDC

40

- Target met for SiC; target not met for GaN
- SiC: 200, 325, 450, and 650 VDC
- GaN: 200, 325, and 450 VDC

POWER FACTOR OF LOAD, TARGET > 0.8

- Target met for SiC; target not met for GaN
- SiC: 0.75 lagging to 1.0
- GaN: No load

MAXIMUM CURRENT PER PHASE, TARGET = 400 Arms

- Target met for SiC; target not met for GaN
- SiC: > 200 Arms was all that was required to achieve 30 kW continuous & 55 kW peak; module met this target
- GaN: < 25 Arms

PRE-CHARGE TIME – 0 TO 200 VDC, TARGET = 2 SECONDS

- Target met for SiC; target met for GaN
- SiC: < 1 second
- GaN: < 1 second

OUTPUT CURRENT RIPPLE – PEAK TO PEAK, TARGET \leq 3% OF FUNDAMENTAL PEAK

- Target met for SiC; target not met for GaN
- SiC: 2.5% of the fundamental peak
- GaN: NA

MAXIMUM SWITCHING FREQUENCY, TARGET = 20 kHz

- Target met for SiC; target met for GaN
- SiC: 20 kHz
- GaN: 20 kHz

CURRENT LOOP BANDWIDTH, TARGET = 2 kHz

- Target met for SiC; target met for GaN
- SiC: 4 kHz
- GaN: 4 kHz

MAXIMUM FUNDAMENTAL ELECTRICAL FREQUENCY, TARGET = 1000 Hz

- Target met for SiC; target not met for GaN
- SiC: 3000 Hz
- GaN: NA

MINIMUM ISOLATION IMPEDANCE – INPUT AND PHASE TERMINALS TO GROUND, TARGET $\geq 1 \text{ M}\Omega$

- Target met for SiC; target met for GaN
- SiC: $> 1 \text{ M}\Omega$
- GaN: $> 1 \text{ M}\Omega$

MINIMUM MOTOR INPUT INDUCTANCE, TARGET = 0.5 mH

- Target met for SiC; target met for GaN
- SiC: 0.55 mH tested
- GaN: 0.55 mH tested

AMBIENT OPERATING TEMPERATURE, TARGET = -40 TO +140 °C

- Target met for SiC; target not met for GaN
- SiC: +140 °C
- GaN: RT